TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MH165FK

8-Bit Shift Register (P-In, S-Out)

The TC7MH165FK is an advanced high speed CMOS 8-bit parallel/serial-in, serial-out shift register fabricated with silicon gate $\rm C^2MOS$ technology.

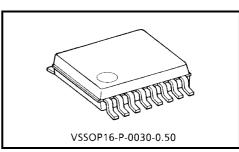
It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

It consists of parallel-in or serial-in, serial-out 8-bit shift register with a gated clock input. When the SHIFT/ \overline{LOAD} input is held high, the serial data input is enabled and the eight flip-flops perform serial shifting with each clock pulse.

When the SHIFT/LOAD input is held low, the parallel data is loaded synchronously into the register at positive going transition of the clock pulse.

The CK-INH input should be shifted high only when the CK input is held high.

An Input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and on two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.



Weight: 0.02 g (typ.)

Features

- High speed: $f_{max} = 150 \text{ MHz}$ (typ.) (VCC = 5 V)
- Low power dissipation: $ICC = 4 \mu A \text{ (max) (Ta} = 25 \text{°C)}$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: $t_pLH \approx t_pHL$
- Wide operating voltage range: VCC (opr) = 2~5.5 V
- Pin and function compatible with 74ALS165

000630EBA

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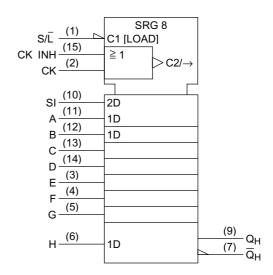
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Pin Assignment (top view)

$\text{S}/\bar{\text{L}}$ 16 V_{CC} CK CK INH Е D F С 13 G В Н 6 Α $\overline{\mathtt{Q}}_{\mathsf{H}}$ SI 10 GND 8 Q_H

IEC Logic Symbol



Truth Table

		Inputs		Internal	Outputs	Outputs					
Shift/ LOAD	CK INH	CK	Serial In	Parallel AH	Q _A	Q _B	Q _H	Q _H			
L	Х	Х	Х	ah	а	b	h	h			
Н	L		Н	Х	Н	Q _{An}	Q _{Gn}	Q _{Gn}			
Н	L		L	Х	L	Q _{An}	Q _{Gn}	$\overline{\overline{Q}}_{Gn}$			
Н	_	L	Н	Х	Н	Q _{An}	Q _{Gn}	\overline{Q}_Gn			
Н		L	L	Х	L	Q _{An}	Q _{Gn}	$\overline{\overline{Q}}_{Gn}$			
Н	Х	Н	Х	Х	No change						
Н	Н	Х	Х	Х	No change						

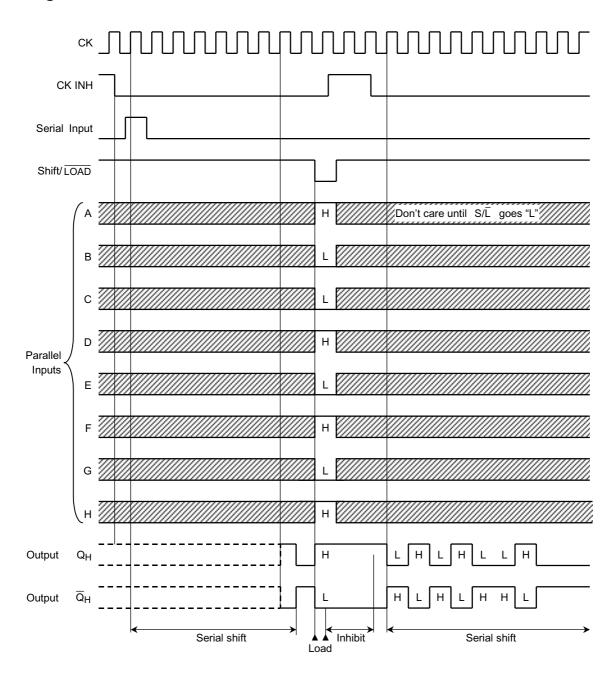
X: Don't care

ah: The level of steady state input voltage at inputs A through H respectively

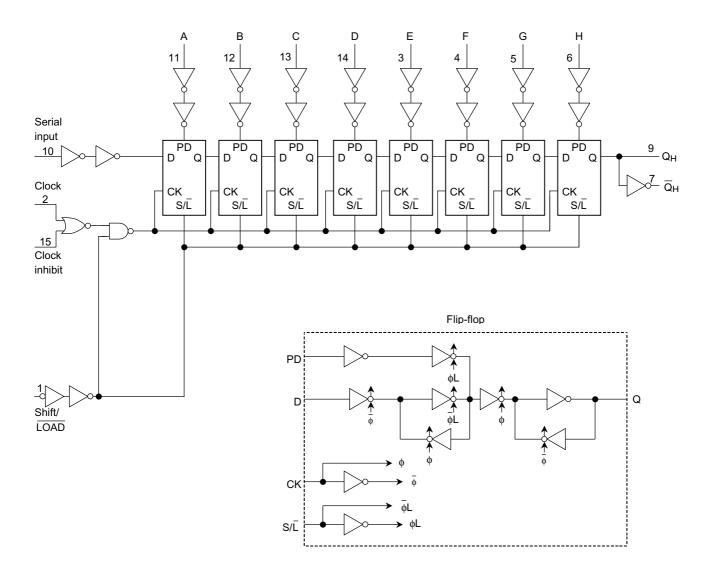
 Q_{An} - Q_{Gn} : The level of Q_{A} - Q_{G} , respectively, before the most recent positive transition of the CK.



Timing Chart



System Diagram





Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	٧
Input diode current	I _{IK}	-20	mA
Output diode current	I _{OK}	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±50	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	-65~150	°C

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0~5.5	V
Input voltage	V _{IN}	0~5.5	V
Output voltage	V _{OUT}	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	$0\sim100 \text{ (V}_{CC} = 3.3 \pm 0.3 \text{ V)}$ $0\sim20 \text{ (V}_{CC} = 5 \pm 0.5 \text{ V)}$	ns/V

Electrical Characteristics

DC Characteristics

Characteristics		Symbol	bol Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Characte	Characteriotics				V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
lanut valtaga		V _{IH}	_		2.0	1.50	_	_	1.50	_	V
	High level				3.0~5.5	$\begin{matrix} V_{CC} \\ \times 0.7 \end{matrix}$	_	_	V _{CC} ×0.7	_	
Input voltage					2.0	_	_	0.50	_	0.50	
	Low level	V _{IL}			_	Max — —					
	High level				2.0	1.9	2.0	_	1.9	_	
		V _{ОН}	or V _{IL}	$I_{OH} = -50 \mu A$	3.0	2.9	3.0	_	2.9	_	V
					4.5	4.4	4.5	_	4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	_	
Output voltage				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	
Output Voltage					2.0	_	0	0.1	_	0.1	v
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 50 \mu A$	3.0	_	0	0.1	_	0.1	
					4.5		0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_	_	0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5			0.36	_	0.44	
Input leakage current		I _{IN}	V _{IN} = 5.5 V or GND		0~5.5	_		±0.1	_	±1.0	μΑ
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		5.5			4.0		40.0	μΑ



Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition	Ta = 25°C		Ta = -40~85°C	Unit		
Characteristics	Symbol	rest Condition	V _{CC} (V)	Тур.	Limit	Limit	Offic	
Minimum pulse width	t _{w (L)}		3.3 ± 0.3	_	6.0	7.0		
(CK, CK INH)	t _{w (H)}	_	5.0 ± 0.5	_	4.0	4.0	ns	
Minimum pulse width	t		3.3 ± 0.3		7.5	9.0	no	
(S/L)	t _{W (L)}		5.0 ± 0.5		5.0	6.0	ns	
Minimum set-up time	+		3.3 ± 0.3	_	7.5	8.5	ns	
(A~H- S/L)	t _s	_	5.0 ± 0.5	_	5.0	5.0		
Minimum set-up time	+		3.3 ± 0.3	_	5.0	6.0	ns	
(SI-CK, CK INH)	t _s	_	5.0 ± 0.5	_	4.0	4.0	lis	
Minimum set-up time	+		3.3 ± 0.3	_	5.0	6.0	no	
(S/L-CK, CK INH)	t _s	_	5.0 ± 0.5	_	4.0	4.0	ns	
Minimum hold time	4.		3.3 ± 0.3	_	0.5	0.5	no	
(A~H- S/L)	t _h	_	5.0 ± 0.5	_	1.0	1.0	ns	
Minimum hold time	4.		3.3 ± 0.3	_	0	0	ns	
(SI-CK, CK INH)	t _h		5.0 ± 0.5		0.5	0.5	115	
Minimum hold time	+.		3.3 ± 0.3		0	0	ns	
(S/L -CK, CK INH)	t _h		5.0 ± 0.5		0.5	0.5	115	
Minimum removal time			3.3 ± 0.3		5.0	5.0		
(CK INH-CK)	t _{rem}	_	5.0 ± 0.5	_	3.5	3.5	ns	
(CK-CK INH)			3.0 ± 0.5	_	3.3	3.0		



AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

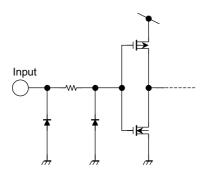
Characteristics	Symbol Test Condition				Ta = 25°C			Ta = -4	0~85°C	Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Unit
		pLH	3.3 ± 0.3	15	_	9.9	15.4	1.0	18.0	- - ns
Propagation delay time	t _{pLH}			50	_	12.4	18.9	1.0	21.5	
(CK, CK INH-Q _H , \overline{Q}_H)	t _{pHL}	<u>—</u>	5.0 ± 0.5	15		6.6	9.9	1.0	11.5	
			3.0 ± 0.5	50		8.1	11.9	1.0	13.5	
			3.3 ± 0.3	15		9.9	15.8	1.0	18.5	- ns
Propagation delay time	t _{pLH}		3.3 ± 0.3	50		12.4	19.3	1.0	22.0	
$(S/L-Q_H, \overline{Q}_H)$	t _{pHL}	_	5.0 ± 0.5	15		6.7	9.9	1.0	11.5	
			3.0 ± 0.5	50		8.2	11.9	1.0	13.5	
	t _{pLH} t _{pHL}	_	3.3 ± 0.3	15		9.2	14.1	1.0	16.5	ns
Propagation delay time			0.0 ± 0.0	50		11.7	17.6	1.0	20.0	
$(H-Q_H, \overline{Q}_H)$			5.0 ± 0.5	15		5.9	9.0	1.0	10.5	
				50		7.4	11.0	1.0	12.5	
		3.3 ± 0.3	15	65	85		55	_		
Maximum clock frequency			3.3 ± 0.3	50	60	105		50	_	- MHz
Maximum clock frequency	f _{max}	<u>—</u>	5.0 ± 0.5	15	110	150	_	90	_	
			J.U ± 0.5	50	95	130		85	_	
Input capacitance	C _{IN}	-				4	10	_	10	pF
Power dissipation capacitance	C _{PD}			(Note)	_	50	_	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

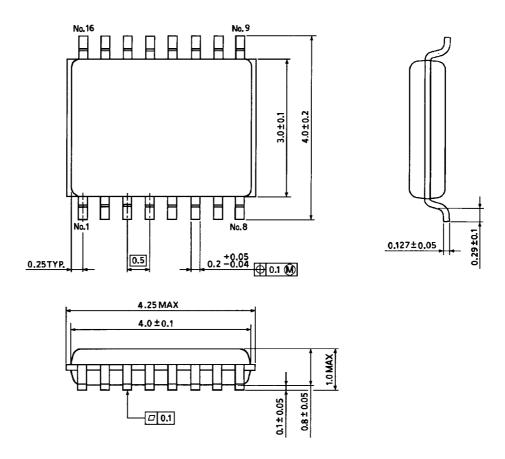
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

Input Equivalent Circuit



Package Dimensions



Weight: 0.02 g (typ.)